

TO-92 Plastic-Encapsulated Transistors

2N4401 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM} : 0.625 \text{ W (Tamb=25°C)}$$

Collector current

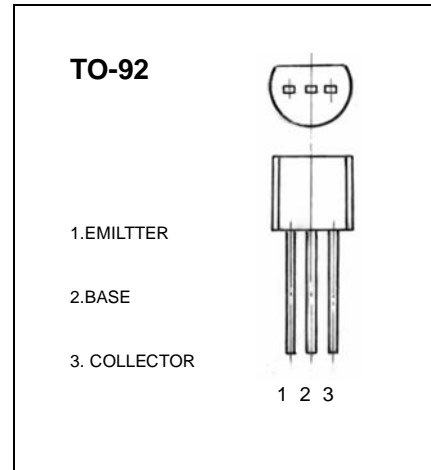
$$I_{CM} : 0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=35\text{V}, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$		0.1	μA
DC current gain	h_{FE1}	$V_{CE}=1\text{V}, I_C=150\text{mA}$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.95	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=20\text{mA}$ $f=100\text{MHz}$	250		MHz